

MOS INTEGRATED CIRCUIT

 μ PD17P228

4-BIT SINGLE-CHIP MICROCONTROLLER FOR SMALL GENERAL-PURPOSE INFRARED REMOTE CONTROLLER

DESCRIPTION

The μ PD17P228 is a model of the μ PD17228 with a one-time PROM instead of an internal mask ROM.

Since the user can write programs to the μ PD17P228, it is ideal for experimental production or small-scale production of the μ PD17225, 17226, 17227 or 17228 systems.

When reading this document, also read the documents related to the μ PD17225, 17226, 17227 and 17228.

Detailed functions are described in the following user's manual. Read this manual when designing your system. μ PD172 $\times\times$ Series User's Manual: U12795E

FEATURES

- Pin compatible with μPD17225, 17226, 17227 and 17228 (except PROM programming function)
- · Carrier generator circuit for infrared remote controller (REM output)
- 17K architecture: General-purpose register method
- Program memory (one-time PROM): 16 Kbytes (8192 × 16)
- Data memory (RAM): 223 × 4 bits
- Pull-up resistor can be connected to RESET pin
- Low-voltage detection circuit (WDOUT output)
- Supply voltage: $V_{DD} = 2.2$ to 3.6 V (fx = 4 MHz: high-speed mode, 4 μ s) $V_{DD} = 3.0$ to 3.6 V (fx = 8 MHz: high-speed mode, 2 μ s)

APPLICATIONS

Preset remote controllers, toys, and portable systems

ORDERING INFORMATION

Part Number	Package
μPD17P228MC-5A4	30-pin plastic SSOP (7.62 mm (300))

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

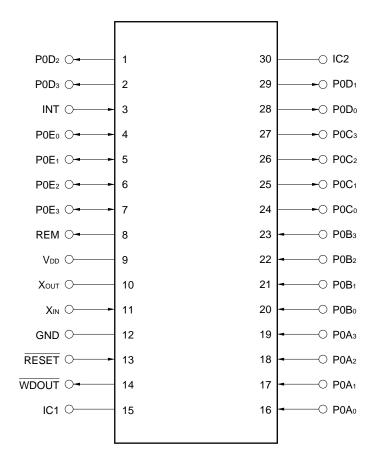
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



PIN CONFIGURATION (TOP VIEW)

30-pin plastic SSOP (7.62 mm (300))
 μPD17P228MC-5A4

(1) Normal oprating mode



GND : Ground

IC1, IC2 : Internally connected Note

INT : External interrupt request signal input

 $\begin{array}{lll} P0A_0\text{-}P0A_3 & : & Input \ port \ (CMOS \ input) \\ P0B_0\text{-}P0B_3 & : & Input \ port \ (CMOS \ input) \end{array}$

P0C₀-P0C₃ : Output port (N-ch open-drain output) P0D₀-P0D₃ : Output port (N-ch open-drain output) P0E₀-P0E₃ : I/O port (CMOS push-pull output)

REM : Remote controller output (CMOS push-pull output)

RESET : Reset input

VDD : Power supply

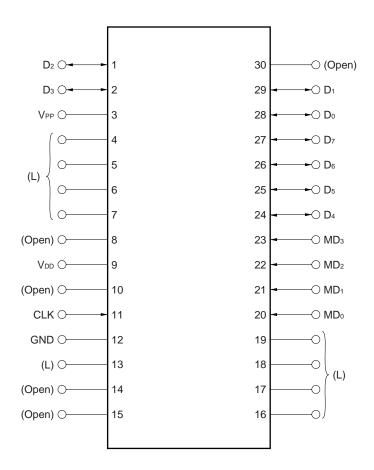
WDOUT : Hang-up/low voltage detection output (N-ch open-drain output)

XIN, XOUT : Resonator connection

Note This pin cannot be used. Leave unconnected.



(2) PROM programming mode



Caution Contents in parantheses indicate how to handle unused pins in PROM programming mode. L :Connect to GND via a resistor (470 Ω) separately. OPEN:Leave unconnected.

CLK : Clock input for PROM
Do - D7 : Data input/output for PROM

GND : Ground

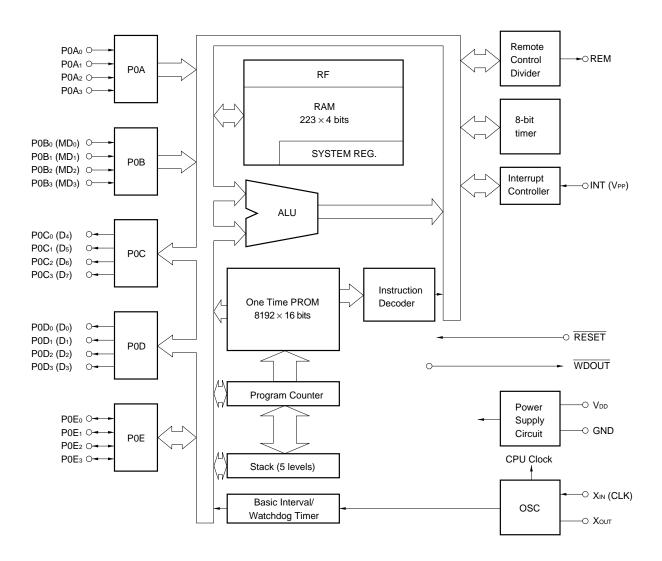
MD₀ - MD₃ : Mode select input for PROM

V_{DD} : Power supply

VPP : Power supply for PROM writing



BLOCK DIAGRAM



Remark (): during PROM programming mode



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1. DIFFERENCES AMONG μ PD17225, 17226, 17227, 17228 AND μ PD17P228

 μ PD17P228 is equipped with PROM to which data can be written by the user instead of the internal mask ROM (program memory) of the μ PD17228.

Table 1-1 shows the differences between the μ PD17225, 17226, 17227, 17228 and μ PD17P228.

The differences among these five models are the program memory and mask option, and their CPU functions and internal hardware are identical. Therefore, the μ PD17P228 can be used to evaluate the program developed for the μ PD17225, 17226, 17227, and 17228 system. **Note, however, that some of the electrical specifications such as supply current and low-voltage detection voltage of the \muPD17P228 are different from those of the \muPD17225, 17226, 17227, and 17228.**

Table 1-1. Differences among μ PD17225, 17226, 17227, 17228 and μ PD17P228

Product Name	μPD17P228	μPD17225	μPD17226	μPD17227	μPD17228
Program memory	One-time PROM		Mask ROM		
	16 K bytes (8192 × 16) (0000H-1FFFH)	4 K bytes (2048 × 16) (0000H-07FFH)	8 K bytes (4096 × 16) (0000H-0FFFH)	12 K bytes (6144 × 16) (0000H-17FFH)	16 K bytes (8192 × 16) (0000H-1FFFH)
Data memory	223 × 4 bits	111 ×	4 bits	223 ×	4 bits
Pull-up resistor of RESET Pin	Provided		Any (mas	sk option)	
Low-voltage detector circuit ^{Note}	Provided		Any (mas	sk option)	
VPP pin, operation mode select pin	Provided		Not pr	ovided	
Instruction execution time (tcy)	2 μs		2 μs (VDD =	2.2 to 3.6 V)	
	$(V_{DD} = 3.0 \text{ to } 3.6 \text{ V})$		4 μ s (VDD =	2.0 to 3.6 V)	
	4 μs				
	$(V_{DD} = 2.2 \text{ to } 3.6 \text{ V})$				
	16 μs				
	$(V_{DD} = 2.2 \text{ to } 3.6 \text{ V})$				
Operation when P0C, P0D are standby		Retain output lev	el immediately befo	re standby mode	
Supply voltage	V _{DD} = 2.0 to 3.6 V		V _{DD} = 2.0) to 3.6 V	
Package	30-pin plastic SSOP (7.62 mm (300))	• 28-pin plastic SDIP (10.16 mm (400))			

Note Although the circuit configuration is identical, its electrical characteristics differ depending on the product.



2. PIN FUNCTIONS

2.1 Normal Operation Mode

Pin No.	Symbol	Function	Output Format	At Reset
16 17 18 19	P0A ₀ P0A ₁ P0A ₂ P0A ₃	4-bit CMOS input port with pull-up resistor. Can be used for key return input of key matrix. When at least one of these pins goes low, standby function is released.	-	Input
20 21 22 23	P0B ₀ P0B ₁ P0B ₂ P0B ₃	4-bit CMOS input port with pull-up resistor. Can be used for key return input of key matrix. When at least one of these pins goes low, standby function is released.	-	Input
24 25 26 27	P0C ₀ P0C ₁ P0C ₂ P0C ₃	4-bit N-ch open-drain output port. Can be used for key source output of key matrix.	N-ch open-drain	Low-level output
28 29 1 2	P0D ₀ P0D ₁ P0D ₂ P0D ₃	4-bit N-ch open-drain output port. Can be used for key source output of key matrix.	N-ch open-drain	Low-level output
4 5 6 7	P0E ₀ P0E ₁ P0E ₂ P0E ₃	4-bit input/output port. Can be set in input or output mode in 1-bit units. In output mode, this port functions as a high current CMOS output port. In input mode, function as CMOS input and can be specified to connect pull-up resistor by program.	CMOS push-pull	Input
8	REM	Outputs transfer signal for infrared remote controller. Active-high output.	CMOS push-pull	Low-level output
13	RESET	System reset input. CPU can be reset when low-level signal is input to this pin. While low-level signal is input, oscillator is stopped. This pin connected to pull-up resistor by mask option.	-	Input
9	V _{DD}	Power supply	_	_
12	GND	Ground	-	-
3	INT	External interrupt request signal input	-	Input
14	WDOUT	Output detecting hang-up and drop in supply voltage. This pin outputs at low level either when an overflow occurs in the watchdog timer, when an overflow/underflow occurs in the stack, or when the supply voltage drops below a specified level. Connect this pin to the RESET pin.	N-ch open-drain	High- impedance Low-level output at low voltage detection
11 10	XIN Xout	Connects ceramic resonator for system clock oscillation	_	(Oscillation stops)
15 30	IC1 IC2	These pins cannot be used. Leave open.	_	-



2.2 PROM Programming Mode

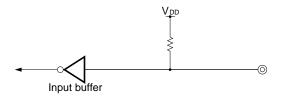
Pin No.	Symbol	Function	Output Format	At Reset
3	Vpp	Power supply for PROM programming. Apply +12.5 V to this pin as the program voltage when writing/ verifying program memory.	-	-
9	VDD	Power supply. Apply +6 V to this pin when writing/verifying program memory.	-	_
11	CLK	Inputs clock for PROM programming.	-	-
12	GND	Ground.	-	-
20 23	MD₀ MD₃	Input pins used to select operation mode when PROM is programmed.	-	Input
24 27 28 29 1	D4 D7 D0 D1 D2 D3	Input/output 8-bit data for PROM programming	CMOS push-pull	Input

Remark The other pins are not used in the PROM programming mode. How to handle the other opins are described in the section **PIN CONFIGURATION (2) PROM programming mode**.

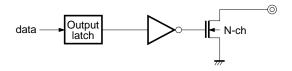
2.3 Input/Output Circuits

The equivalent input/output circuit for each μ PD17P228 pin is shown below.

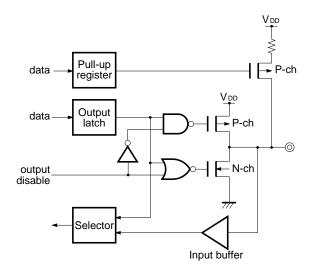
(1) P0A, P0B



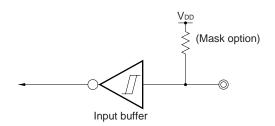
(2) POC, POD



(3) P0E

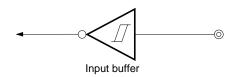


(4) RESET



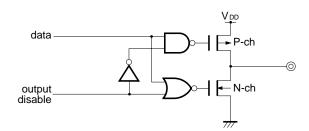
Schmitt trigger input with hysteresis characteristics

(5) INT

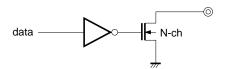


Schmitt trigger input with hysteresis characteristics

(6) REM



(7) WDOUT





2.4 Processing of Unused Pins

Process the unused pins as follows:

Table 2-1. Processing of Unused Pins

Pin	Recommended Connection
P0A ₀ -P0A ₃	Connect to V _{DD} .
P0B ₀ -P0B ₃	Connect to V _{DD} .
P0C ₀ -P0C ₃	Connect to GND.
P0D ₀ -P0D ₃	Connect to GND.
P0E ₀ -P0E ₃	Input : Individually connect to VDD or GND via resistor. Output : Leave open.
REM	Leave open.
INT	Connect to GND.
WDOUT	Connect to V _{DD} via resistor.
IC1, IC2	These pins cannot be used. Leave open.

2.5 Notes on Using the RESET and INT Pins

In addition to the functions shown in **2. PIN FUNCTION**, the $\overline{\text{RESET}}$ pin also has the function of setting a test mode (for IC testing) in which the internal operations of the $\mu\text{PD17P228}$ are tested.

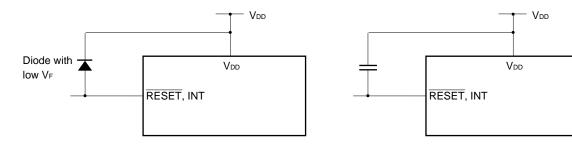
When a voltage higher than V_{DD} is applied to either of these pins, the test mode is set. This means that, even during normal operation, the μ PD17P228 may be set in the test mode if noise exceeding V_{DD} is applied.

For example, if the wiring length of the RESET or INT pin is too long, noise superimposed on the wiring line of the pin may cause the above problem.

Therefore, keep the wiring length of these pins as short as possible to suppress the noise; otherwise, take noise preventive measures as shown below by using external components.

Connect diode with low V_F between V_{DD} and RESET/INT pin

• Connect capacitor between VDD and RESET/INT pin



Connect the WDOUT and RESET pins since a low level is output after the test mode is set using the INT pin.



3. WRITING AND VERIFYING ONE-TIME PROM (PROGRAM MEMORY)

The program memory of the $\mu PD17P228$ is a one-time PROM of 8192 \times 16 bits.

To write or verify this one-time PROM, the pins shown in Table 3-1 are used. Note that no address input pin is used. Instead, the address is updated by using the clock input from the CLK pin.

Table 3-1. Pins Used to Write/Verify Program Memory

Pin Name	Function
VPP	Supplies voltage when writing/verifying program memory.
	Apply +12.5 V to this pin.
V _{DD}	Power supply.
	Supply +6 V to this pin when writing/verifying program memory.
CLK	Inputs clock to update address when writing/verifying program memory.
	By inputting pulse four times to CLK pin, address of program memory is updated.
MD ₀ -MD ₃	Input to select operation mode when writing/verifying program memory.
D ₀ -D ₇	Inputs/outputs 8-bit data when writing/verifying program memory.

3.1 Operating Mode When Writing/Verifying Program Memory

The μ PD17P228 is set in the program memory write/verify mode when +6 V is applied to the V_{DD} pin and +12.5 V is applied to the V_{PP} pin after the μ PD17P228 has been in the reset status (V_{DD} = 5 V, \overline{RESET} = 0 V) for a specific time. In this mode, the operating modes shown in Table 3-2 can be set by setting the MD₀ through MD₃ pins. Leave all the pins other than those shown in Table 3-1 unconnected or connect them to GND via pull-down resistor (470 Ω). (Refer to **PIN CONNECTION (2) PROM programming mode.)**

Table 3-2. Setting Operation Mode

		Setting of Op	erating Mode	Setting of Operating Mode						
V_{PP}	VPP VDD MD0 MD1 MD2 MD3									
+12.5 V	+6 V	Н	L	Н	L	Program memory address 0 clear mode				
		L	Н	Н	Н	Write mode				
		L	L	Н	Н	Verify mode				
		Н	×	Н	Н	Program inhibit mode				

x: don't care (L or H)

Data Sheet U14542EJ1V0DS00 11

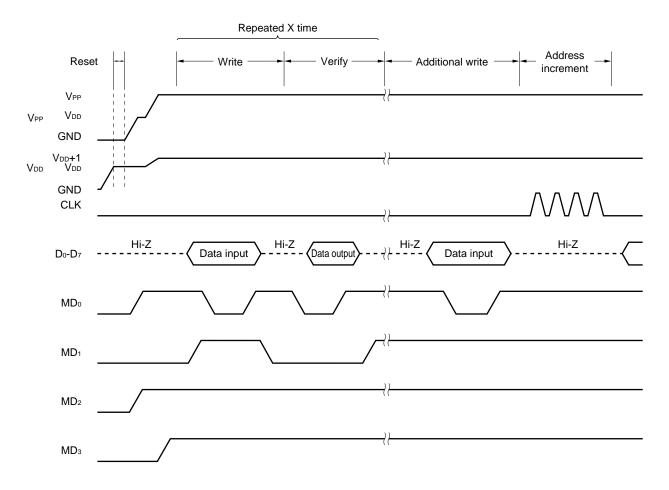


3.2 Program Memory Writing Procedure

The program memory is written at high speed in the following procedure.

- (1) Pull down the pins not used to GND via resistor. Keep the CLK pin low.
- (2) Supply 5 V to the VDD pin. Keep the VPP pin low.
- (3) Supply 5 V to the VPP pin after waiting for 10 μ s.
- (4) Set the program memory address 0 clear mode by using the mode setting pins.
- (5) Supply +6 V to VDD and +12.5 V to VPP.
- (6) Set the program inhibit mode.
- (7) Write data to the program memory in the 1-ms write mode.
- (8) Set the program inhibit mode.
- (9) Set the verify mode. If the data have been written to the program memory, proceed to (10). If not, repeat steps (7) through (9).
- (10) Additional writing of (number of times of writing in (7) through (9): $X \times 1$ ms.
- (11) Set the program inhibit mode.
- (12) Input a pulse to the CLK pin four times to update the program memory address (+1).
- (13) Repeat steps (7) through (12) up to the last address.
- (14) Set the 0 clear mode of the program memory address.
- (15) Change the voltages on the VDD and VPP pins to 5 V.
- (16) Turn off power.

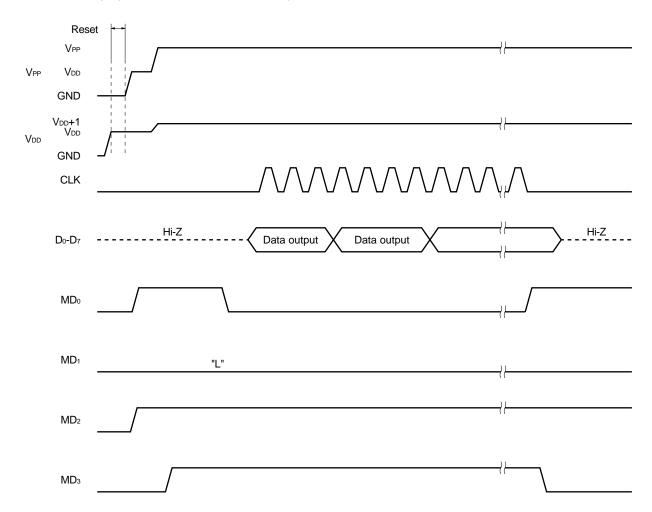
The following figure illustrates steps (2) through (12) above.



3.3 Program Memory Reading Procedure

- (1) Pull down the pins not used to GND via resistor. Keep the CLK pin low.
- (2) Supply 5 V to the VDD pin. Keep the VPP pin low.
- (3) Supply 5 V to the VPP pin after waiting for 10 μ s.
- (4) Set the program memory address 0 clear mode by using the mode setting pins.
- (5) Supply +6 V to VDD and +12.5 V to VPP.
- (6) Set the program inhibit mode.
- (7) Set the verify mode. Data of each address is output sequentially each time the clock pulse is input to the CLK pin four times.
- (8) Set the program inhibit mode.
- (9) Set the program memory address 0 clear mode.
- (10) Change the voltage on the VDD and VPP pins to 5 V.
- (11) Turn off power.

The following figure illustrates steps (2) through (9) above.





4. ELECTRICAL SPECIFICATIONS

Absolute Maximum Ratings ($T_A = 25^{\circ}C$)

Item	Symbol			Ratings	Unit
Supply voltage	V _{DD}			-0.3 to +7.0	V
PROM power supply	VPP			-0.3 to +13.5	V
Input voltage	Vı			-0.3 to V _{DD} + 0.3	V
Output voltage	Vo			-0.3 to V _{DD} + 0.3	V
High-level output current ^{Note}	Іон	REM pin	Peak value	-36.0	mA
			rms value	-24.0	mA
		1 pin (P0E pin)	Peak value	-7.5	mA
			rms value	-5.0	mA
		Total of P0E pins	Peak value	-22.5	mA
			rms value	-15.0	mA
Low-level output current Note	lol	1 pin (P0C, P0D, P0E,	Peak value	7.5	mA
		REM or WDOUT pin)	rms value	5.0	mA
		Total of P0C, P0D,	Peak value	22.5	mA
		WDOUT pins	rms value	15.0	mA
		Total of P0E pins	Peak value	30.0	mA
			rms value	20.0	mA
Operating temperature	TA		•	-40 to +85	°C
Storage temperature	Tstg			-65 to +150	°C
Power dissipation	Pd	T _A = 85°C		180	mW

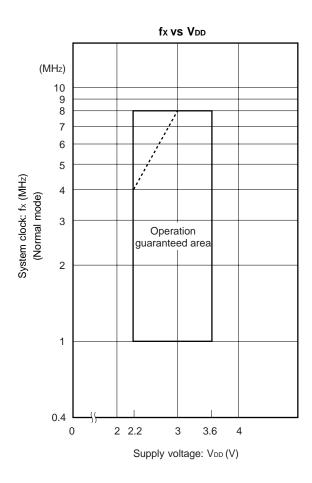
Note Calculate rms value by this expression: [rms value] = [Peak value] $\times \sqrt{\text{Duty}}$

Caution Even if one of the parameters exceeds its absolute maximum rating even momentarily, the quality of the product may be degraded. The absolute maximum rating therefore specifies the upper or lower limit of the value at which the product can be used without physical damages. Be sure not to exceed or fall below this value when using the product.

Recommended Operating Ranges (TA = -40 to +85°C, VDD = 2.2 to 3.6 V)

Item	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Supply voltage	V _{DD1}	fx = 1 MHz	High-speed mode (Instruction execution time: 16 μ s)	2.2		3.6	V
	V _{DD2}	fx = 4 MHz	Ordinary mode (Instruction execution time: 4 μ s)				
	VDD3	fx = 8 MHz	High-speed mode (Instruction execution time: 4 μ s)				
	V _{DD4}		High-speed mode (Instruction execution time: 2 μ s)	3.0		3.6	V
Oscillation frequency	fx			1.0	4.0	8.0	MHz
Operating temperature	TA			-40	+25	+85	°C
Low-voltage detector circuit ^{Note}	Тсч			4		32	μs

Note Reset if the status of $V_{DD} = 2.05 \text{ V}$ (TYP.) lasts for 1 ms or longer. Program hang-up does not occur even if the voltage drops, until the reset function is effected (when the \overline{RESET} pin and \overline{WDOUT} pin are connected). Some oscillators stop oscillating before the reset function is effected.



Remark The region indicated by the broken line in the above figure is the guaranteed operating range in the high-speed mode.

System Clock Oscillator Characteristics (TA = -40 to +85°C, VDD = 2.2 to 3.6 V)

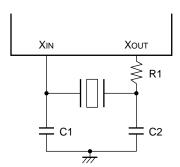
Resonator	Recommended Constants	Item	Conditions	MIN.	TYP.	MAX.	Unit
Ceramic resonator	X _{IN} X _{OUT}	Oscillation frequency (fx) ^{Note 1}		1.0	4.0	8.0	MHz
		Oscillation stabilization time ^{Note 2}	After V _{DD} reached MIN. in oscillation voltage range			4	ms

- **Notes 1.** The oscillation frequency only indicates the oscillator characteristics.
 - 2. The oscillation stabilization time is necessary for oscillation to be stabilized, after VDD application or STOP mode release.

Caution To use a system clock oscillator circuit, perform the wiring in the area enclosed by the dotted line in the above figure as follows, to avoid adverse wiring capacitance influences:

- · Keep wiring length as short as possible.
- Do not cross a signal line with some other signal lines. Do not route the wiring in the vicinity of lines through which a large current flows.
- Always keep the oscillator capacitor ground at the same potential as GND. Do not ground the capacitor to a ground pattern, through which a large current flows.
- · Do not extract signals from the oscillator.

External circuit example



Remark To select a resonator and determine oscillator constants, please evaluate the oscillation yourself or request the resonator manufacturer to evaluate it.



DC Characteristics (T_A = -40 to +85°C, V_{DD} = 2.2 to 3.6 V)

Item	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
High-level input voltage	V _{IH1}	RESET, INT			0.8V _{DD}		V _{DD}	V
	V _{IH2}	P0A, P0B			0.7VDD		V _{DD}	V
	VIH3	P0E			0.8V _{DD}		V _{DD}	V
Low-level input voltage	VIL1	RESET, INT			0		0.2V _{DD}	V
	VIL2	P0A, P0B			0		0.3VDD	V
	VIL3	P0E			0		0.35Vpd	V
High-level input leakage current	Ішн	P0A, P0B, P0E, RESET, INT	VIH = VDD				3	μΑ
Low-level input leakage	ILIL1	INT	VIL = 0 V				-3	μΑ
current	ILIL2	P0E	VIL = 0 V w/o pull-	up resistor			-3	μΑ
High-level output leakage current	Ісон	POC, POD, POE, WDOUT	Voh = Vdd				3	μΑ
Low-level output leakage current	ILOL	P0E, WDOUT	Vol = 0 V w/o pul	I-up resistor			-3	μΑ
Internal pull-up resistor	R ₁	P0E, RESET			25	50	100	kΩ
	R ₂	P0A, P0B			100	200	400	kΩ
High-level output current	Іон1	REM	Vон = 1.0 V, VDD =	3 V	-6	-13	-24	mA
High-level output voltage	Vон	P0E, REM	Iон = −0.5 mA		VDD-0.3		V _{DD}	V
Low-level output voltage	V _{OL1}	POC, POD, REM, WDOUT	IoL = 0.5 mA		0		0.3	V
	V _{OL2}	P0E	IoL = 1.5 mA		0		0.3	V
Low-voltage detector circuit	VDT	WDOUT = low level	V _{DT} = V _{DD}			2.05	2.2	V
Data retention voltage	V _{DDDR}	RESET = low leve	el or STOP mode		1.3		3.6	V
Supply current	I _{DD1}	Operating mode	V _{DD} = 3 V ± 10%	fx = 1 MHz		0.55	1.1	mA
		(high-speed)		fx = 4 MHz		1.0	2.0	mA
				fx = 8 MHz		1.3	2.6	mA
	I _{DD2}	Operating mode	V _{DD} = 3 V ± 10%	fx = 1 MHz		0.5	1.0	mA
		(low-speed)		fx = 4 MHz		0.75	1.5	mA
				fx = 8 MHz		0.9	1.8	mA
	IDD3	HALT mode	V _{DD} = 3 V ± 10%	fx = 1 MHz		0.4	0.8	mA
				fx = 4 MHz		0.5	1.0	mA
				fx = 8 MHz		0.6	1.2	mA
	I _{DD4}	STOP mode	V _{DD} = 3 V ± 10%			2.0	20.0	μΑ
			built-in POC	T _A = 25 °C		2.0	5.0	μΑ

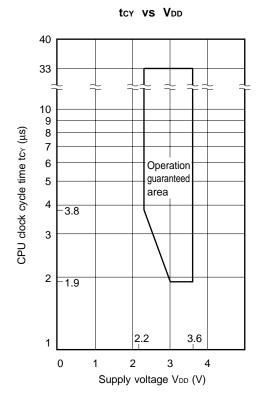


AC Characteristics (T_A = -40 to +85°C, V_{DD} = 2.2 to 3.6 V)

Item	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU clock cycle time ^{Note} (instruction execution time)	tcY1		3.8		33	μs
	tcY2	V _{DD} = 3.0 to 3.6 V	1.9		33	μs
INT high/low level width	tinth, tintl		20			μs
RESET low level lwidth	trsl		10			μs

Note The CPU clock cycle time (instruction execution time) is determined by the oscillation frequency of the resonator connected and SYSCK (RF: address 02H) of the register file.

The figure on the right shows the CPU clock cycle time toy vs. supply voltage V_{DD} characteristics.





DC Programming Characteristics (T_A = 25 °C, V_{DD} = 6.0 \pm 0.25 V, V_{PP} = 12.5 \pm 0.3 V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
High-level input voltage	V _{IH1}	Other than CLK	0.7 Vdd		V _{DD}	V
	V _{IH2}	CLK	V _{DD} -0.5		V _{DD}	V
Low-level input voltage	V _{IL1}	Other than CLK	0		0.3 VDD	V
	V _{IL2}	CLK	0		0.4	V
Input leakage current	lu	VIN = VIL OR VIH			10	μΑ
High-level output voltage	Vон	Iон = −1 mA	V _{DD} -1.0			V
Low-level output voltage	Vol	IoL = 1.6 mA			0.4	V
V _{DD} supply current	IDD				30	mA
VPP supply current	IPP	MD0 = VIL, MD1 = VIH			30	mA

Cautions 1. Keep VPP to within +13.5 V including overshoot.

2. Apply VDD before VPP and turns it off after VPP.

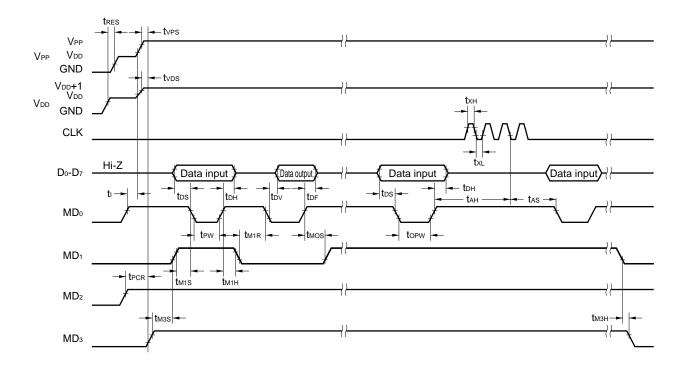
AC Programming Characteristics (TA = 25°C, VDD = 6.0 \pm 0.25 V, VPP = 12.5 \pm 0.3 V)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Address setup time ^{Note} (vs. MD₀↓)	tas		2			μs
MD₁ setup time (vs. MD₀↓)	t _{M1S}		2			μs
Data setup time (vs. MD₀↓)	tos		2			μs
Address hold time ^{Note} (vs. MD ₀ ↑)	t AH		2			μs
Data hold time (vs. MD₀↑)	tон		2			μs
MD ₀ ↑→ data output float delay time	tor		0		130	ns
V _{PP} setup time (vs. MD₃↑)	tvps		2			μs
V _{DD} setup time (vs. MD₃↑)	tvds		2			μs
Initial program pulse width	t PW		0.95	1.0	1.05	ms
Additional program pulse width	topw		0.95		21.0	ms
MD₀ setup time (vs. MD₁↑)	tмos		2			μs
MD₀↓→ data output delay time	t DV	MD0 = MD1 = VIL			1	μs
MD₁ hold time (vs. MD₀↑)	t м1н	tм1H+tм1R ≥ 50 μs	2			μs
MD₁ recovery time (vs. MD₀↓)	t M1R		2			μs
Program counter reset time	t PCR		10			μs
CLK input high-, low-level width	txH, txL		0.125			μs
CLK input frequency	fx				4.19	MHz
Initial mode set time	tı		2			μs
MD₃ setup time (vs. MD₁↑)	tмзs		2			μs
MD₃ hold time (vs. MD₁↓)	tмзн		2			μs
MD₃ setup time (vs. MD₀↓)	t _{M3SR}	When program memory is read	2			μs
Address ^{Note} → data output delay time	t DAD	When program memory is read			2	μs
Address ^{Note} → data output hold time	t HAD	When program memory is read	0		130	ns
MD₃ hold time (vs. MD₀↑)	tмзнк	When program memory is read	2			μs
MD₃↓→ data output float delay time	tdfr	When program memory is read			2	μs
Reset setup time	tres		10			μs

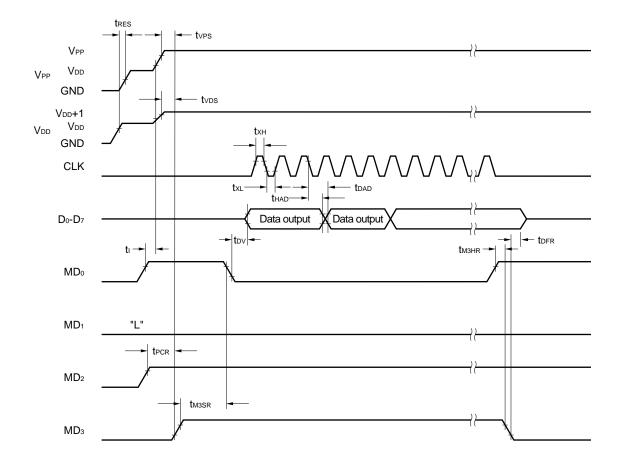
Notes The internal address increment (+1) is performed on the fall of the 3rd clock, where 4 clocks compreise one cycle. The internal clock is not connected to a pin.



Program Memory Write Timing

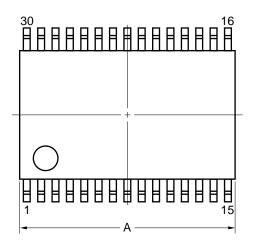


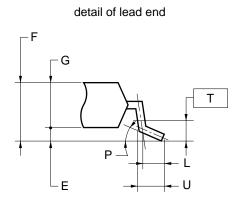
Program Memory Read Timing

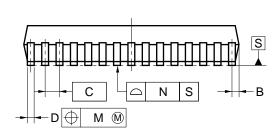


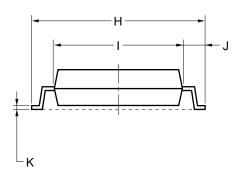
5. PACKAGE DRAWING

30-PIN PLASTIC SSOP (7.62 mm (300))









NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	9.85±0.15
В	0.45 MAX.
С	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
Е	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
М	0.13
N	0.10
Р	3°+5°
Т	0.25
U	0.6±0.15

S30MC-65-5A4-2



6. RECOMMENDED SOLDERING CONDITIONS

For the μ PD17P228 soldering must be performed under the following conditions.

For details of recommended conditions for surface mounting, refer to information document "Semiconductor Device Mounting Technology Manual" (C10535E).

For other soldering methods, please consult with NEC personnel.

Table 6-1. Soldering Conditions of Surface Mount Type

• μPD17P228MC-5A4: 30-pin plastic SSOP (7.62 mm(300))

Soldering Method	Soldering Conditions	Symbol
Infrated Reflow	Package peak temperature: 235°C, Time: 30 seconds max. (210°C min.), Number of times: 2 max. Number of days: 3 (after that, prebaking is necessary at 125°C for 10 hours)	IR35-103-2
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (200°C min.), Number of times: 2 max. Number of days: 3 (after that, prebaking is necessary at 125°C for 10 hours)	VP15-103-2
Wave soldering	Solder bath temperature: 260°C max, Time: 10 seconds max., Number of times: once, preheating temperature: 120°C max. (package surface temperature) Number of days: 3 (after that, prebaking is necessary at 125°C for 10 hours)	WS-60-103-1
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per side of device)	_

Note Number of days in storage after the dry pack has been opened. The storage conditions are at 25°C, 65% RH MAX.

Caution Do not use two or more soldering methods in combination (except the partial heating method).



APPENDIX. DEVELOPMENT TOOLS

To develop the programs for the μ PD17P228 subseries, the following development tools are available:

Hardware

Name	Remarks
In-circuit emulator (IE-17K, IE-17K-ETNote 1)	IE-17K and IE-17K-ET are the in-circuit emulators used in common with the 17K series microcontroller. IE-17K and IE-17K-ET are connected to a PC-9800 series or IBM PC/AT TM compatible machines as the host machine with RS-232C. By using these in-circuit emulators with a system evaluation board corresponding to the microcomputer, the emulators can emulate the microcomputer. A higher level debugging environment can be provided by using man-machine interface SIMPLEHOST TM .
SE board (SE-17225)	This is an SE board for μ PD17225 subseries. It can be used alone to evaluate a system or in combination with an in-circuit emulator for debugging.
Emulation probe (EP-17K30GS)	EP-17K30GS is an emulation probe for 17K series 30-pin SSOP (MC-5A4). When used with EV-9500GT-30 ^{Note 2} , it connects an SE board to the target system.
Conversion adapter (EV-9500GT-30 ^{Note 2})	The EV-9500GT-30 is a conversion adapter for the 30-pin SSOP (MC-5A4). It is used to connect the EP-17K30GS and target system.
PROM programmer (AF-9706 ^{Note 3} , AF-9708 ^{Note 3} , AF-9709 ^{Note 3})	AF-9706, AF-9708, and AF-9709 are PROM programmers corresponding to μ PD17P228. By connecting program adapter PA-17P236 to this PROM programmer, μ PD17P228 can be programmed.
Program adapter (PA-17P236)	PA-17P236 are adapters that is used to program μ PD17P228, and is used in combination with AF-9706, AF-9708, or AF-9709.

Notes 1. Low-cost model: External power supply type

- 2. Two EV-9500GT-30 are supplied with the EP-17K30GS. Five EV-9500GT-30s are optionally available as a set.
- **3.** These are products from Ando Electric Co., Ltd. For details, consult Ando Electric Co., Ltd. (Tel: 03-3733-1166).



Software

Name	Outline	Host Machine	os	Supply	Order Code
17K assembler (RA17K)	The RA17K is an assembler common to the 17K series products. When developing the program of devices, RA17K is used in combination with a device file (AS17225).	PC-9800 series	Japanese Windows TM	3.5" 2HD	μSAA13RA17K
		compatible	Japanese Windows	3.5" 2HC	μSAB13RA17K
			English Windows		μSBB13RA17K
Device file (AS17225)	The AS17225 is a device file for μ PD17225, 17226, 17227, and 17228 and is used in combination with an assembler for the 17K series (RA17K).	PC-9800 series	Japanese Windows	3.5" 2HD	μSAA13AS17225
		IBM PC/AT compatible machine	Japanese Windows	3.5" 2HC	μSAB13AS17225
			English Windows		μSBB13AS17225
Support software	SIMPLEHOST is a software package that enables man-machine in-	PC-9800 series	Japanese Windows	3.5" 2HD	μSAA13ID17K
(SIMPLEHOST)	terface on the Windows when a program is developed by using an incircuit emulator and a personal computer.	IBM PC/AT compatible	Japanese Windows	3.5" 2HC	μSAB13ID17K
		machine	English Windows		μSBB13ID17K

NOTES FOR CMOS DEVICES -

1 PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

Regional Information

Some information contained in this document may vary from country to country. Before using any NEC product in your application, please contact the NEC office in your country to obtain a list of authorized representatives and distributors. They will verify:

- · Device availability
- Ordering information
- · Product release schedule
- · Availability of related technical literature
- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)
- · Network requirements

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